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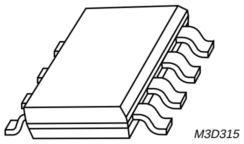


PHK12NQ03LT

N-channel TrenchMOS™ logic level FET

Rev. 02 — 02 March 2004 | Product data

1. Product profile

1.1 Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

1.2 Features

- Low on-state resistance
- Fast switching.

1.3 Applications

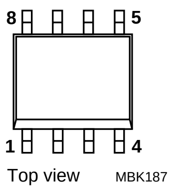
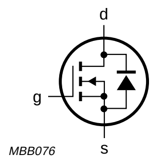
- DC-to-DC converters
- Portable equipment applications.

1.4 Quick reference data

- $V_{DS} \leq 30$ V
- $P_{tot} \leq 2.5$ W
- $I_D \leq 11.8$ A
- $R_{DSon} \leq 14$ mΩ

2. Pinning information

Table 1: Pinning - SOT96-1 (SO8), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1,2,3	source (s)		
4	gate (g)		
5,6,7,8	drain (d)		

SOT96-1 (SO8)

3. Ordering information

Table 2: Ordering information

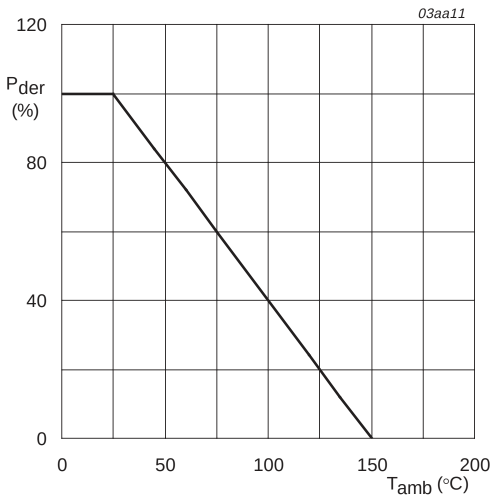
Type number	Package		
	Name	Description	Version
PHK12NQ03LT	SO8	Plastic small outline package; 8 leads	SOT96

4. Limiting values

Table 3: Limiting values

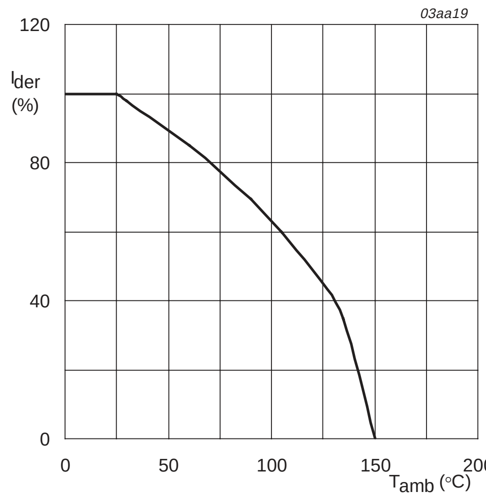
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	25 °C ≤ T_j ≤ 150 °C	-	30	V
V_{GS}	gate-source voltage		-	±20	V
I_D	drain current	T_{amb} = 25 °C; pulsed; t_p ≤ 10 s; Figure 2 and 3	-	11.8	A
I_{DM}	peak drain current	T_{amb} = 25 °C; pulsed; t_p ≤ 10 µs; Figure 3	-	35.3	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; pulsed; t_p ≤ 10 s; Figure 1	-	2.5	W
T_{stg}	storage temperature		–55	+150	°C
T_j	junction temperature		–55	+150	°C
Source-drain diode					
I_S	source (diode forward) current	T_{amb} = 25 °C; pulsed; t_p ≤ 10 s	-	11.8	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; I_D = 7.7 A; t_p = 2.35 ms; V_{DD} ≤ 30 V; V_{GS} = 10 V; starting T_j = 25 °C	-	440	mJ



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

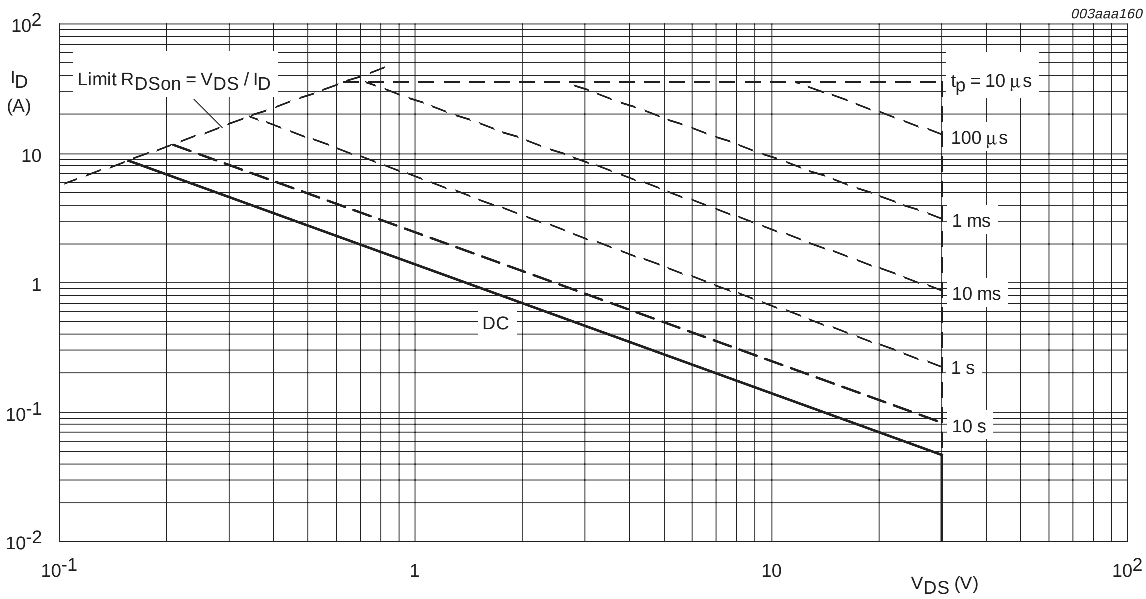
Fig 1. Normalized total power dissipation as a function of ambient temperature.



$V_{GS} \geq 5$ V

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature.



T_{amb} = 25 °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint; $t_p \leq 10$ s; Figure 4	-	-	50	K/W

5.1 Transient thermal impedance

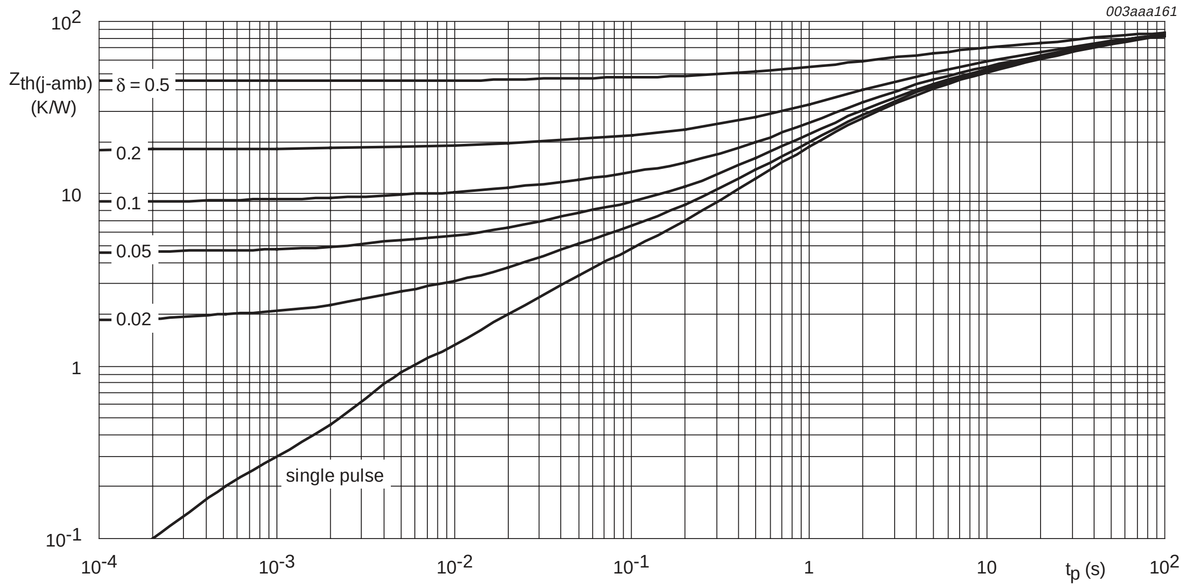


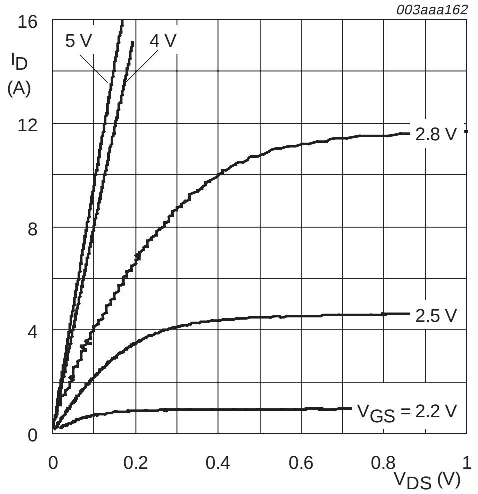
Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration.

6. Characteristics

Table 5: Characteristics

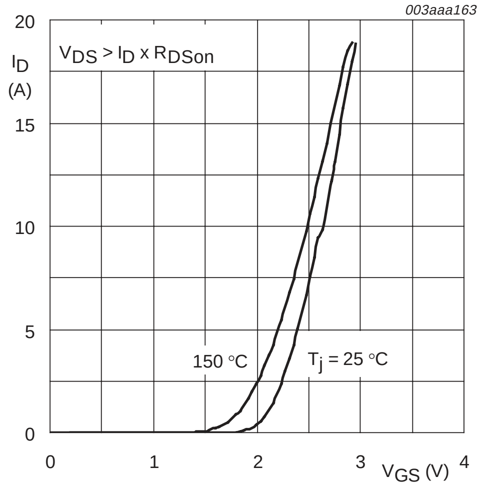
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS}; T_j = 25 °C; Figure 9	1	-	2	V
I_{DSS}	drain-source leakage current	V_{DS} = 24 V; V_{GS} = 0 V				
		T_j = 25 °C	-	-	1	µA
		T_j = 100 °C	-	-	5	µA
I_{GSS}	gate-source leakage current	V_{GS} = ±20 V; V_{DS} = 0 V	-		100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 10 A; Figure 8	-	11	14	mΩ
		V_{GS} = 10 V; I_D = 12 A; Figure 8	-	8.9	10.5	mΩ
Dynamic characteristics						
g_{fs}	forward transconductance	V_{DS} = 15 V; I_D = 10 A;	-	34	-	S
$Q_{g(tot)}$	total gate charge	I_D = 15 A; V_{DD} = 16 V; V_{GS} = 5 V; Figure 13	-	17.6	-	nC
Q_{gs}	gate-source charge		-	4	-	nC
Q_{gd}	gate-drain (Miller) charge		-	4.4	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 16 V; f = 1 MHz; Figure 11	-	1335	-	pF
C_{oss}	output capacitance		-	391	-	pF
C_{rss}	reverse transfer capacitance		-	190	-	pF
$t_{d(on)}$	turn-on delay time	V_{DD} = 16 V; R_D = 10 Ω; V_{GS} = 10 V	-	10.6	-	ns
t_r	rise time		-	11.7	-	ns
$t_{d(off)}$	turn-off delay time		-	37	-	ns
t_f	fall time		-	19	-	ns
Source-drain (reverse) diode						
V_{SD}	source-drain (diode forward) voltage	I_S = 1 A; V_{GS} = 0 V; Figure 12	-	0.7	1.0	V
t_{rr}	reverse recovery time	I_S = 2.3 A; dI_S/dt = –100 A/µs; V_{GS} = 0 V	-	70	-	ns



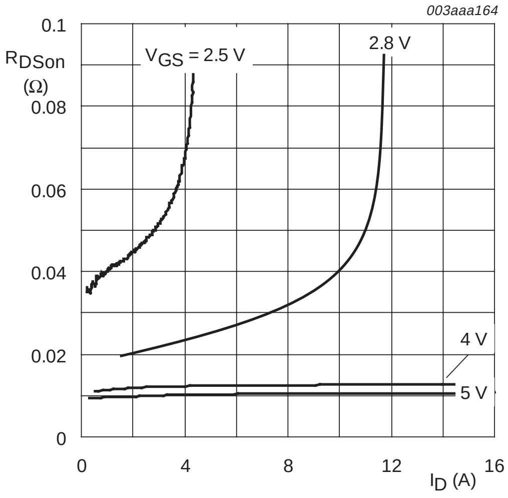
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



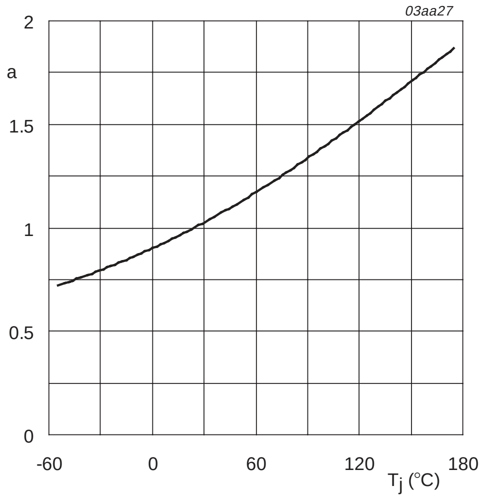
T_j = 25 °C and 150 °C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



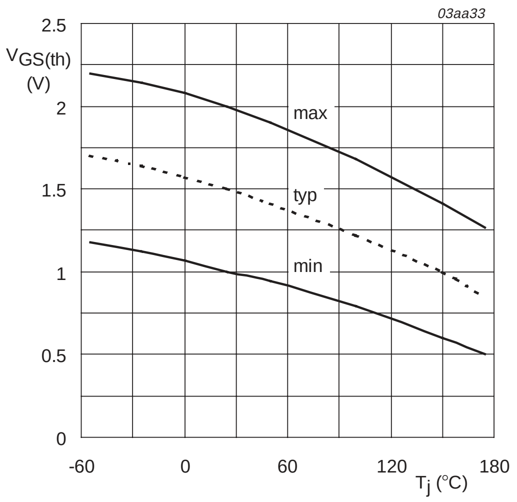
T_j = 25 °C

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



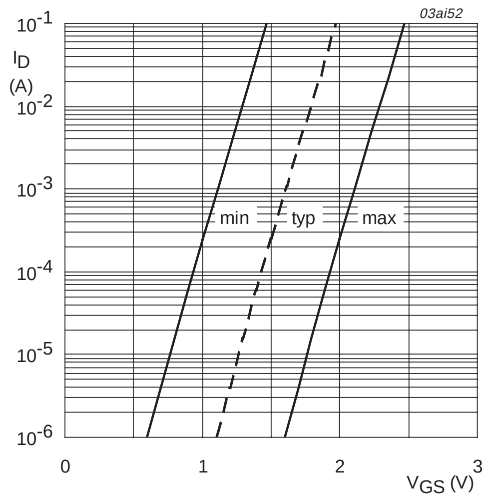
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 8. Normalized drain source on-state resistance factor as a function of junction temperature.



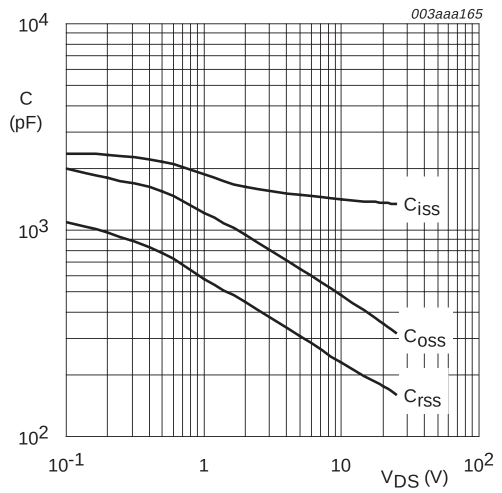
I_D = 250 μA; $V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



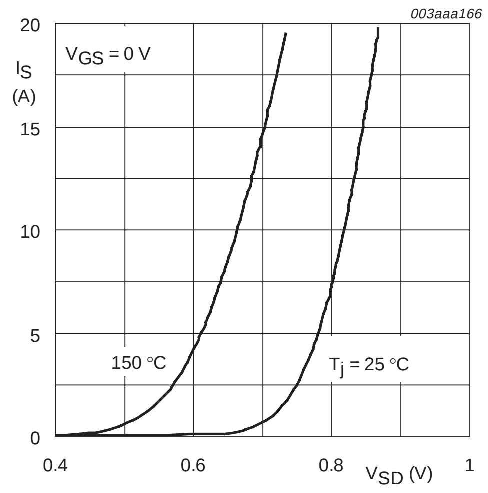
T_j = 25 °C; V_{DS} = 5 V

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



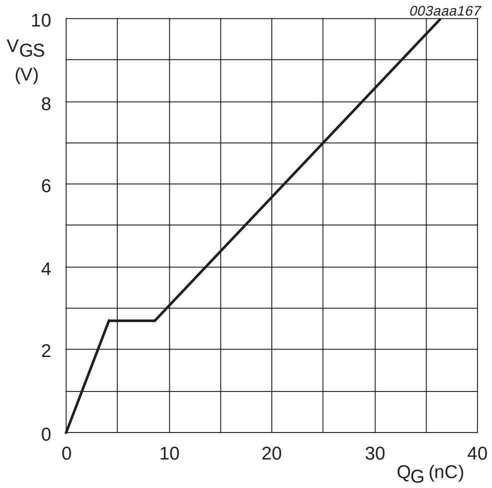
V_{GS} = 0 V; f = 1 MHz

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



T_j = 25 °C and 150 °C; V_{GS} = 0 V

Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

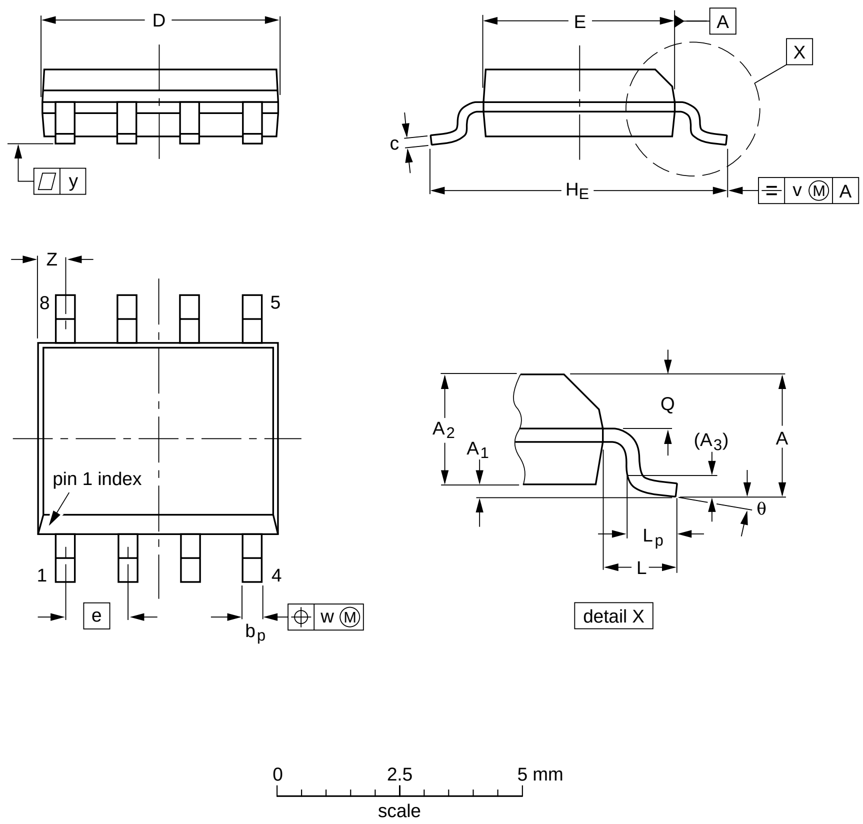


I_D = 15 A; V_{DD} = 16 V

Fig 13. Gate-source voltage as a function of gate charge; typical values.

7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm **SOT96-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D(1)	E(2)	e	H_E	L	L_p	Q	v	w	y	Z(1)	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Notes

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT96-1	076E03	MS-012				~~99-12-27~~ 03-02-18

Fig 14. SOT96-1 (SO8).

8. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
02	20040302	-	**Product data (9397 750 12955)** Modifications • Data sheet updated to latest presentation standards. • Section 1.4 "Quick reference data" correction to I_D value. • Section 4 "Limiting values" I_D, I_{DM}, P_{tot} and I_S conditions and values corrected. • Section 4 "Limiting values" Figure 1, 2 and 3 corrected. • Section 4 "Limiting values" $E_{DS(AL)S}$ added. • Section 5 "Thermal characteristics" typ and max values corrected. • Section 5 "Thermal characteristics" Figure 4 corrected. • Section 6 "Characteristics" Figure 13 corrected.
01	20020322	-	**Product data (9397 750 09405)**

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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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